



FEATURES

Power dissipation SOT-89

P_{CM} : 0.5 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -1 A

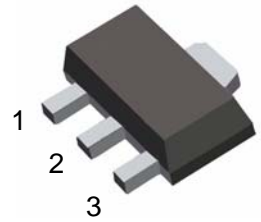
Collector-base voltage

$V_{(BR)CBO}$: -100 V

1. BASE

2. COLLECTOR

3. EMITTER



Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

DEVICE MARKING BCX53=AH BCX53-10=AK BCX53-16=AL

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT	
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-100		V	
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-80		V	
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5		V	
Collector cut-off current	I_{CBO}	$V_{CB}=-30V, I_E=0$		-0.1	μA	
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	μA	
DC current gain	BCX53 BCX53-10 BCX53-16	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-150mA$	63 63 100	250 160 250	
		$h_{FE(2)}$	$V_{CE}=-2V, I_C=-5mA$	63		
		$h_{FE(3)}$	$V_{CE}=-2V, I_C=-500mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$		-0.5	V	
Base-emitter voltage	$V_{BE(ON)}$	$I_C=-500mA, V_{CE}=-2V$		-1	V	
Transition frequency	f_T	$V_{CE}=-5V, I_C=-10mA$ $f = 100MHz$	50		MHz	